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(71) Applicant: **FUJITSU LTD**

(72) Inventor: **EBE KOJI**
MURAKAMI SATOSHI

(54) **SEMICONDUCTOR PHOTODETECTOR**

(57) Abstract:

PURPOSE: To form wiring layers connected to semiconductor layers of which a light receiving part is composed easily and with a high yield and, further, avoid the thermal distortion which is produced in the semiconductor layers of which the light receiving part is composed when the photodetector is used under a heat cycle to suppress the deterioration of device characteristics.

CONSTITUTION: A light receiving part which is composed of semiconductor layers 11 whose p-n junction boundaries are vertical, or approximately vertical, to a semiconductor substrate 1 surface is formed on the semiconductor substrate.

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